

LME49710 High Performance, High Fidelity Audio Operational Amplifier

General Description

The LME49710 is part of the ultra-low distortion, low noise. high slew rate operational amplifier series optimized and fully specified for high performance, high fidelity applications. Combining advanced leading-edge process technology with state-of-the-art circuit design, the LME49710 audio operational amplifiers deliver superior audio signal amplification for outstanding audio performance. The LME49710 combines extremely low voltage noise density (2.5nV/Hz) with vanishingly low THD+N (0.00003%) to easily satisfy the most demanding audio applications. To ensure that the most challenging loads are driven without compromise, the LME49710 has a high slew rate of ±20V/µs and an output current capability of ±26mA. Further, dynamic range is maximized by an output stage that drives $2k\Omega$ loads to within 1V of either power supply voltage and to within 1.4V when driving 600Ω loads.

The LME49710's outstanding CMRR(120dB), PSRR(120dB), and $\rm V_{OS}$ (0.05mV) give the amplifier excellent operational amplifier DC performance.

The LME49710 has a wide supply range of $\pm 2.5 V$ to $\pm 17 V$. Over this supply range the LME49710's input circuitry maintains excellent common-mode and power supply rejection, as well as maintaining its low input bias current. The LME49710 is unity gain stable. The Audio Operational Amplifier achieves outstanding AC performance while driving complex loads with values as high as 100pF.

The LME49710 is available in 8-lead narrow body SOIC, 8-lead plastic DIP, and 8-lead metal can TO-99. Demonstration boards are available for each package.

Key Specifications

Power Supply	Voltage Range	±2.5V to ±17V

■ THD+N ($A_V = 1, V_{OUT} = 3V_{RMS}, f_{IN} = 1kHz$)

$R_L = 2k\Omega$	0.00003% (typ)
$R_L = 600\Omega$	0.00003% (typ)
■ Input Noise Density	2.5nV/ $\sqrt{\text{Hz}}$ (typ)
■ Slew Rate	±20V/µs (typ)
■ Gain Bandwidth Product	55MHz (typ)
■ Open Loop Gain (R _L = 600Ω)	140dB (typ)
■ Input Bias Current	7nA (typ)
■ Input Offset Voltage	0.05mV (typ)
■ DC Gain Linearity Error	0.000009%

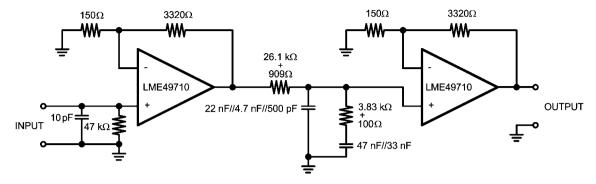
Features

- Easily drives 600Ω loads
- Optimized for superior audio signal fidelity
- Output short circuit protection
- PSRR and CMRR exceed 120dB (typ)
- SOIC, DIP, TO-99 metal can packages

Applications

- Ultra high quality audio amplification
- High fidelity preamplifiers
- High fidelity multimedia
- State of the art phono pre amps
- High performance professional audio
- High fidelity equalization and crossover networks
- High performance line drivers
- High performance line receivers
- High fidelity active filters

Typical Application

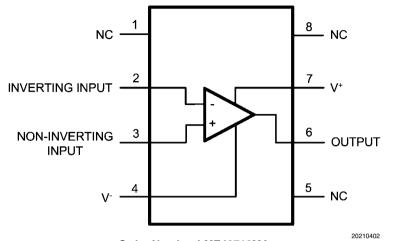


Note: 1% metal film resistors, 5% polypropylene capacitors

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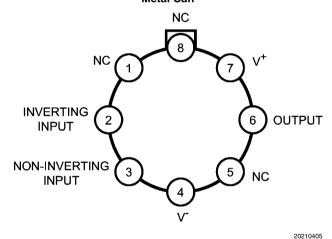
FIGURE 1. Passively Equalized RIAA Phono Preamplifier

Connection Diagrams



Order Number LME49710MA See NS Package Number — M08A Order Number LME49710NA See NS Package Number — N08E

Metal Can



Order Number LME49710HA See NS Package Number — H08C

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Absolute Maximum Ratings (Notes 1, 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Power Supply Voltage (V_S = V⁺ - V⁻) 36V Storage Temperature -65°C to 150°C Input Voltage (V-) - 0.7V to (V+) + 0.7V

Output Short Circuit (Note 3) Continuous Power Dissipation Internally Limited ESD Susceptibility (Note 4) 2000V

ESD Susceptibility (Note 5)	200V			
Junction Temperature	150°C			
Thermal Resistance				
θ_{JA} (SO)	145°C/W			
θ_{JA} (NA)	102°C/W			
θ_{JA} (HA)	150°C/W			
θ_{JC} (HA)	35°C/W			
Temperature Range				
$T_{MIN} \le T_A \le T_{MAX}$	-40 °C \leq T _A \leq 85°C			

 $\pm 2.5 \text{V} \le \text{V}_{\text{S}} \le \pm 17 \text{V}$

Supply Voltage Range

Electrical Characteristics (Notes 1, 2)

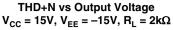
The following specifications apply for $V_S = \pm 15V$, $R_L = 2k\Omega$, $f_{IN} = 1kHz$, and $T_A = 25^{\circ}C$, unless otherwise specified.

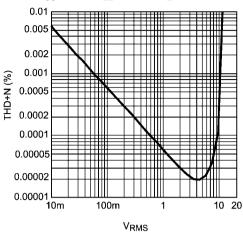
			LME49710		Units
Symbol	Parameter	Conditions	Typical	· · · · · · · · · · · · · · · · · · ·	
			(Note 6)	(Notes 7, 8)	(Limits)
		$A_V = 1$, $V_{OUT} = 3V_{RMS}$			
THD+N	Total Harmonic Distortion + Noise	$R_L = 2k\Omega$	0.00003		% (max)
		$R_L = 600\Omega$	0.00003	0.00009	% (max)
IMD	Intermodulation Distortion	$A_V = 1$, $V_{OUT} = 3V_{RMS}$ Two-tone, 60Hz & 7kHz 4:1	0.00005		% (max)
GBWP	Gain Bandwidth Product		55	45	MHz (min)
SR	Slew Rate		±20	±15	V/µs (min)
FPBW	Full Power Bandwidth	$V_{OUT} = 1V_{P-P}$, $-3dB$ referenced to output magnitude at f = 1kHz	10		MHz
t _s	Settling time	$A_V = 1$, 10V step, $C_L = 100pF$ 0.1% error range	1.2		μs
	Equivalent Input Noise Voltage	f _{BW} = 20Hz to 20kHz	0.34	0.65	μV _{RMS}
e _n	E	f = 1kHz	2.5	4.7	nV/√ Hz
	Equivalent Input Noise Density	f = 10Hz	6.4		nV/√ Hz
i _n		f = 1kHz	1.6		pA / √Hz
	Current Noise Density	f = 10Hz	3.1		pA/√ Hz
V _{OS}	Offset Voltage		±0.05	±0.7	mV (max)
ΔV _{OS} /ΔTemp	Average Input Offset Voltage Drift vs Temperature	40°C ≤ T _A ≤ 85°C	0.2		μV/°C
PSRR	Average Input Offset Voltage Shift vs Power Supply Voltage	ΔV _S = 20V (Note 9)	125	110	dB (min)
I _B	Input Bias Current	$V_{CM} = 0V$	7	72	nA (max)
ΔI _{OS} /ΔTemp	Input Bias Current Drift vs Temperature	–40°C ≤ T _A ≤ 85°C	0.1		nA/°C
I _{os}	Input Offset Current	$V_{CM} = 0V$	5	65	nA (max)
V _{IN-CM}	Common-Mode Input Voltage Range		+14.1 -13.9	(V+) - 2.0 (V-) + 2.0	V (min) V (min)
CMRR	Common-Mode Rejection	-10V <v<sub>CM<10V</v<sub>	120	110	dB (min)
7	Differential Input Impedance		30		kΩ
Z_{IN}	Common Mode Input Impedance	-10V <v<sub>CM<10V</v<sub>	1000		ΜΩ
		$-10V < V_{OUT} < 10V, R_L = 600\Omega$	140		dB
A _{VOL}	Open Loop Voltage Gain	$-10V < V_{OUT} < 10V, R_L = 2k\Omega$	140	125	dB
		$-10V < V_{OUT} < 10V, R_L = 10k\Omega$	140		dB

	ool Parameter	Conditions	LME49710		
Symbol			Typical	cal Limit	Units (Limits)
			(Note 6)	(Notes 7, 8)	
	Maximum Output Voltage Swing	$R_L = 600\Omega$	±13.6	±12.5	V
V_{OUTMAX}		$R_L = 2k\Omega$	±14.0		V
		$R_L = 10k\Omega$	±14.1		V
I _{OUT}	Output Current	$R_L = 600\Omega, V_S = \pm 17V$	±26	±23	mA (min)
1	Short Circuit Current		+53		mA
OUT-CC			-42		mA
	Output Impedance	$f_{IN} = 10kHz$			
R _{OUT}		Closed-Loop	0.01		Ω
		Open-Loop	13		Ω
C _{LOAD}	Capacitive Load Drive Overshoot	100pF	16		%
I _S	Quiescent Current	I _{OUT} = 0mA	4.8	5.5	mA (max)

- Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur.
- **Note 2:** Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions.
- Note 3: Amplifier output connected to GND, any number of amplifiers within a package.
- Note 4: Human body model, 100pF discharged through a $1.5k\Omega$ resistor.
- Note 5: Machine Model ESD test is covered by specification EIAJ IC-121-1981. A 200pF cap is charged to the specified voltage and then discharged directly into the IC with no external series resistor (resistance of discharge path must be under 50Ω).
- Note 6: Typical specifications are specified at +25°C and represent the most likely parametric norm.
- Note 7: Tested limits are guaranteed to National's AOQL (Average Outgoing Quality Level).
- Note 8: Datasheet min/max specification limits are guaranteed by design, test, or statistical analysis.
- Note 9: PSRR is measured as follows: V_{OS} is measured at two supply voltages, $\pm 5V$ and $\pm 15V$. PSRR = $|20log(\Delta V_{OS}/\Delta V_S)|$.

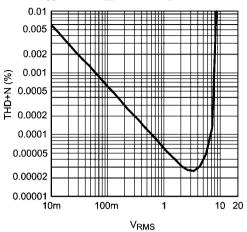
Typical Performance Characteristics





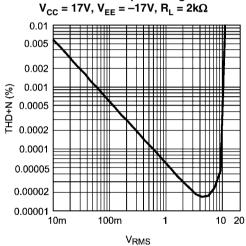
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THD+N vs Output Voltage $V_{CC} = 12V$, $V_{EE} = -12V$, $R_L = 2k\Omega$



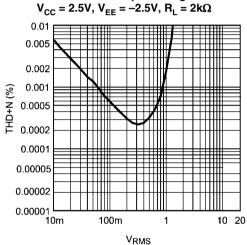
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THD+N vs Output Voltage



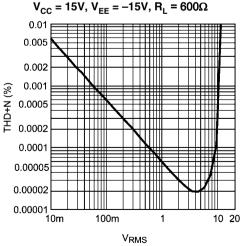
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THD+N vs Output Voltage



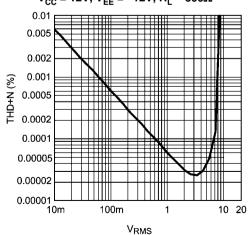
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THD+N vs Output Voltage $V_{co} = 15V$, $V_{cc} = -15V$, $R_c = 6000$

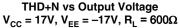


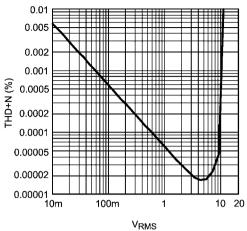
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THD+N vs Output Voltage V_{CC} = 12V, V_{EE} = -12V, R_L = 600 Ω



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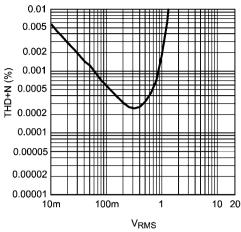




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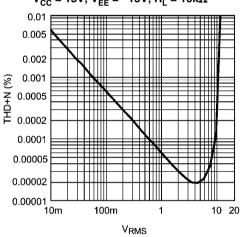
$V_{CC} = 2.5V, V_{EE} = -2.5V, R_{L} = 600\Omega$ 0.01

THD+N vs Output Voltage



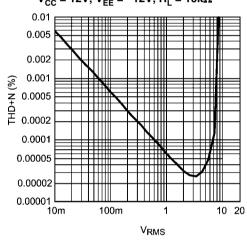
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THD+N vs Output Voltage $V_{CC} = 15V$, $V_{EE} = -15V$, $R_L = 10k\Omega$



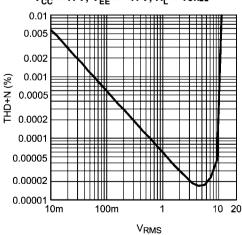
20210477

THD+N vs Output Voltage V_{CC} = 12V, V_{EE} = -12V, R_L = 10k Ω



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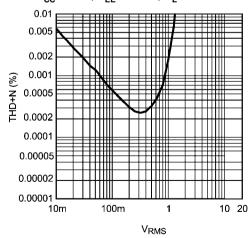
THD+N vs Output Voltage $V_{CC} = 17V, V_{EE} = -17V, R_{L} = 10k\Omega$



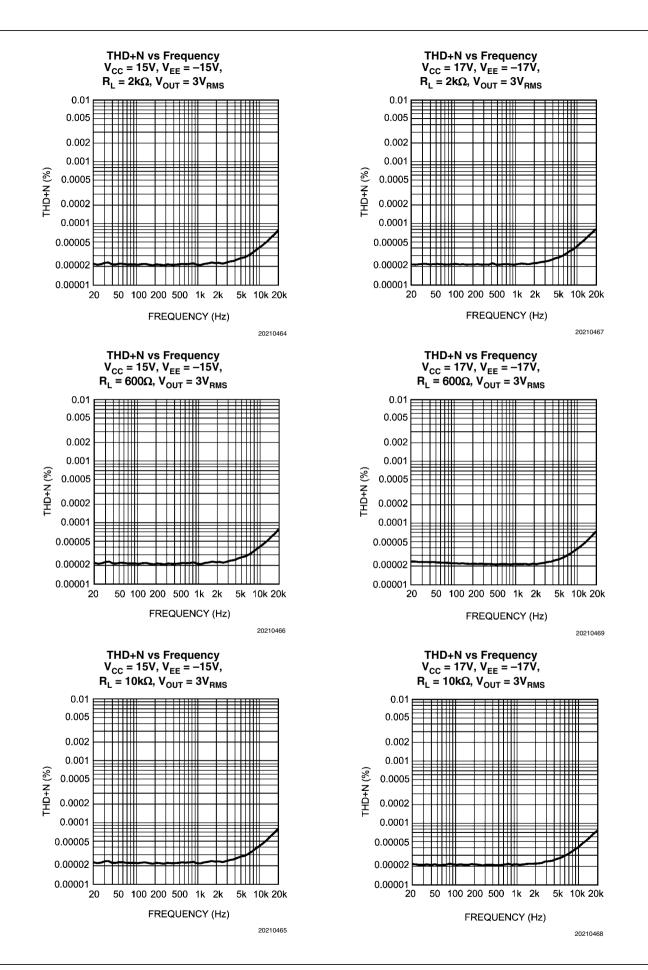
20210480

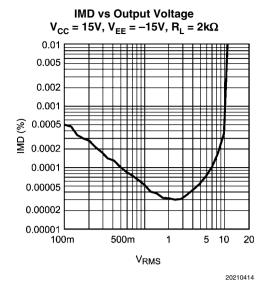
7

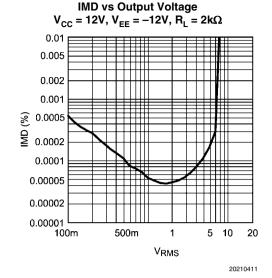
THD+N vs Output Voltage $V_{CC} = 2.5V, V_{EE} = -2.5V, R_{L} = 10k\Omega$



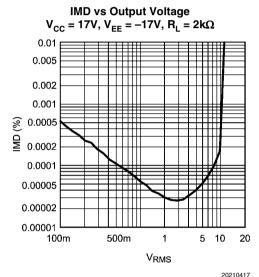
20210471

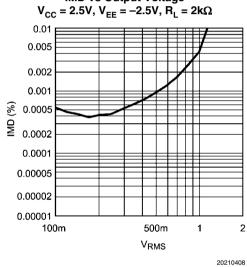




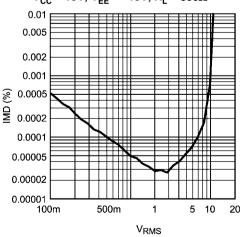


IMD vs Output Voltage





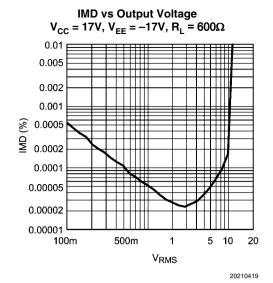
IMD vs Output Voltage $V_{CC} = 15V$, $V_{EE} = -15V$, $R_L = 600\Omega$

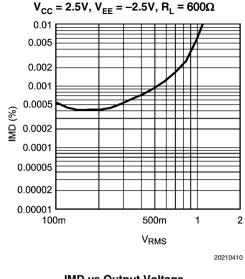


IMD vs Output Voltage $V_{CC} = 12V$, $V_{EE} = -12V$, $R_L = 600\Omega$ 0.01 0.005 0.002 0.001 0.0005 0.0002 0.0001 0.00005 0.00002 0.00001 100m 500m 5 10 20 V_{RMS}

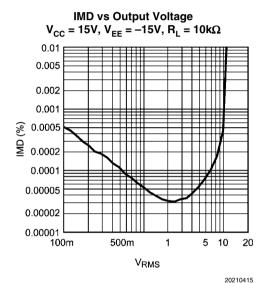
20210413

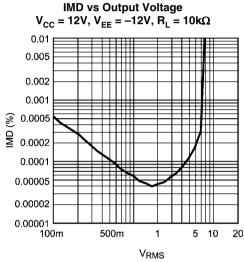
20210416



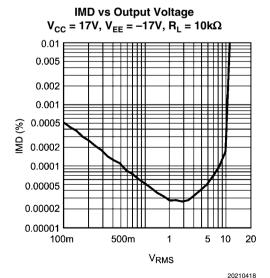


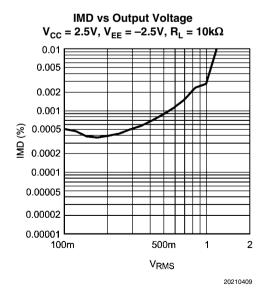
IMD vs Output Voltage



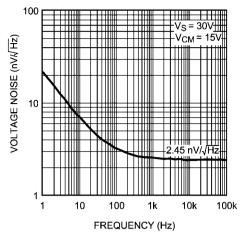


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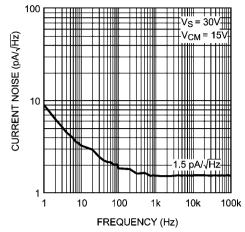


Voltage Noise Density vs Frequency



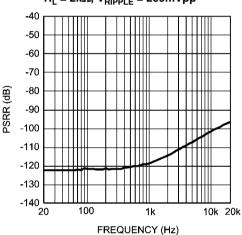
20210490

Current Noise Density vs Frequency



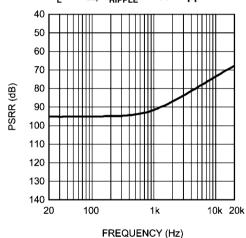
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$\begin{aligned} & \text{PSRR+ vs Frequency} \\ & \text{V}_{\text{CC}} = 2.5\text{V}, \, \text{V}_{\text{EE}} = -2.5\text{V}, \\ & \text{R}_{\text{L}} = 2\text{k}\Omega, \, \text{V}_{\text{RIPPLE}} = 200\text{mVpp} \end{aligned}$



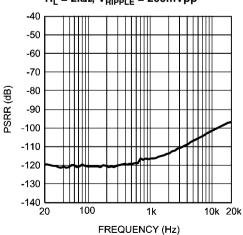
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PSRR- vs Frequency V_{CC} = 2.5V, V_{EE} = -2.5V, R_L = 200mVpp



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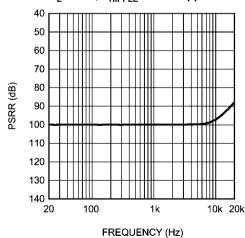
PSRR+ vs Frequency $V_{CC} = 12V$, $V_{EE} = -12V$, $R_{L} = 2k\Omega$, $V_{RIPPIF} = 200mVpp$



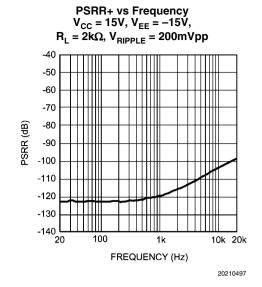
20210494

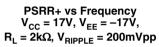
11

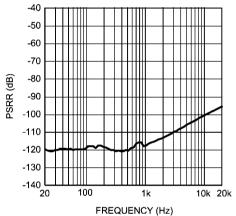
PSRR- vs Frequency $V_{CC} = 12V$, $V_{EE} = -12V$, $R_{L} = 2k\Omega$, $V_{RIPPIF} = 200mVpp$



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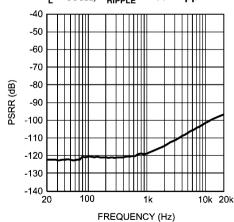




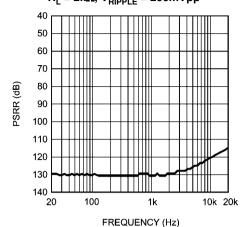
 $\begin{aligned} & \text{PSRR+ vs Frequency} \\ & \text{V}_{\text{CC}} = 2.5\text{V}, \, \text{V}_{\text{EE}} = -2.5\text{V}, \\ & \text{R}_{\text{L}} = 600\Omega, \, \text{V}_{\text{RIPPLE}} = 200\text{mVpp} \end{aligned}$

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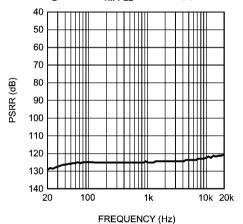


PSRR- vs Frequency V_{CC} = 15V, V_{EE} = -15V, R_L = 2k Ω , V_{RIPPLE} = 200mVpp



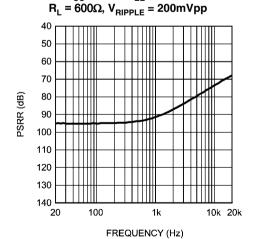
20210425

 $\begin{aligned} & \text{PSRR- vs Frequency} \\ & \text{V}_{\text{CC}} = 17\text{V}, \, \text{V}_{\text{EE}} = -17\text{V}, \\ & \text{R}_{\text{L}} = 2k\Omega, \, \text{V}_{\text{RIPPLE}} = 200\text{mVpp} \end{aligned}$



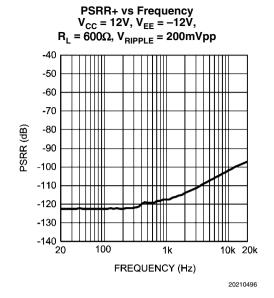
20210438

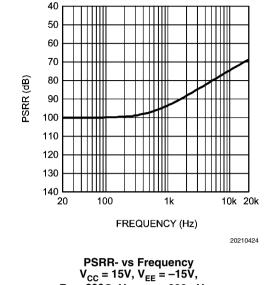
PSRR- vs Frequency



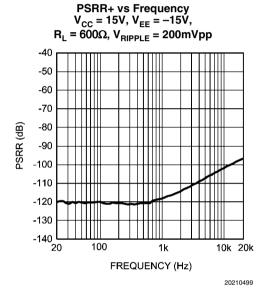
 $V_{CC} = 2.5V, V_{EE} = -2.5V,$

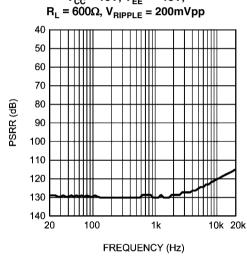
20210421



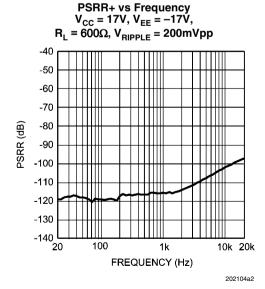


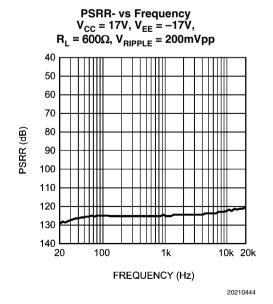
 $\begin{array}{c} \text{PSRR- vs Frequency} \\ \text{V}_{\text{CC}} = 12\text{V}, \, \text{V}_{\text{EE}} = -12\text{V}, \\ \text{R}_{\text{L}} = 600\Omega, \, \text{V}_{\text{RIPPLE}} = 200\text{mVpp} \end{array}$

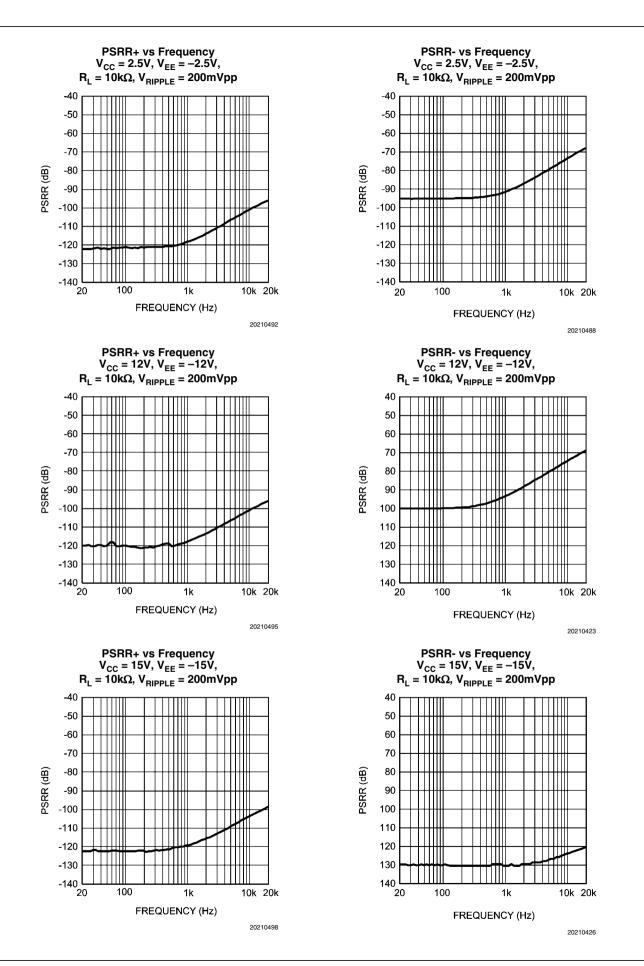


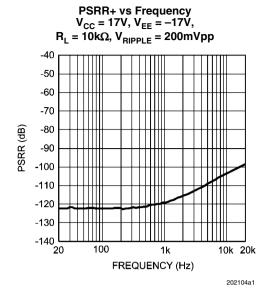


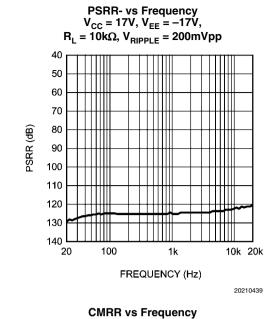
20210451

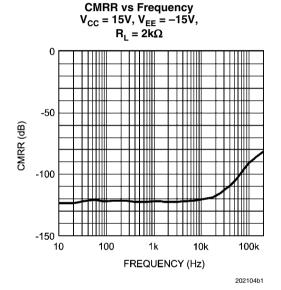


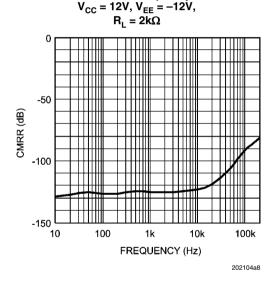


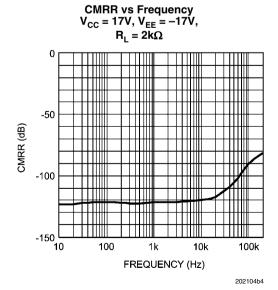


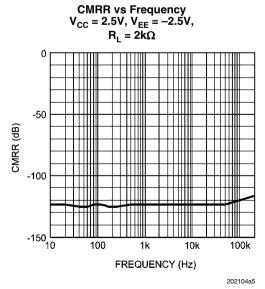


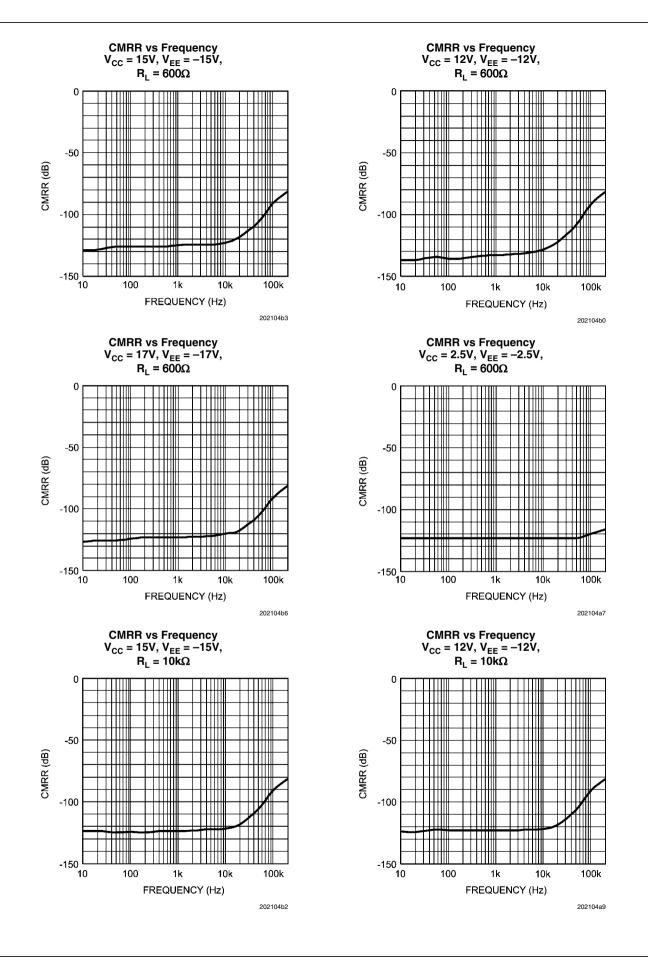


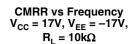


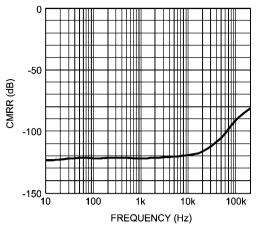








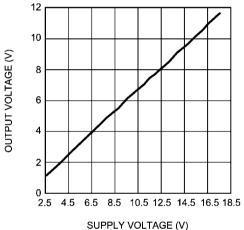




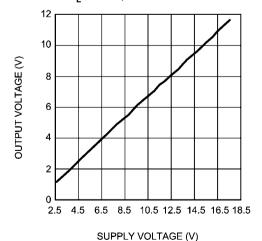
202104b5

20210485

Output Voltage vs Supply Voltage $R_L = 2k\Omega$, THD+N = 1%

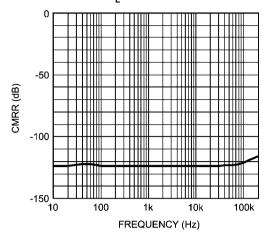


Output Voltage vs Supply Voltage $R_1 = 10k\Omega$, THD+N = 1%



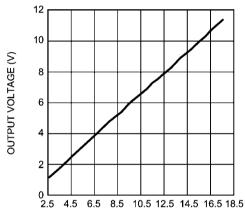
20210486

CMRR vs Frequency V_{CC} = 2.5V, V_{EE} = -2.5V, $R_L = 10k\Omega$



202104a6

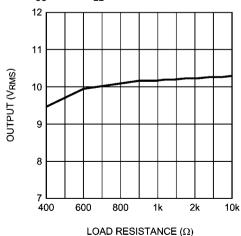
Output Voltage vs Supply Voltage $R_{L} = 600\Omega$, THD+N = 1%



SUPPLY VOLTAGE (V)

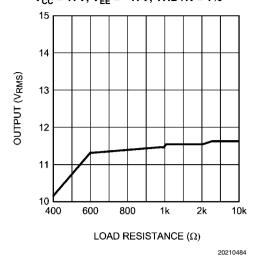
20210487

Output Voltage vs Load Resistance $V_{CC} = 15V, V_{EE} = -15V, THD+N = 1\%$

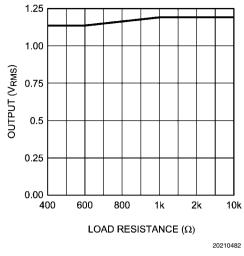


20210483

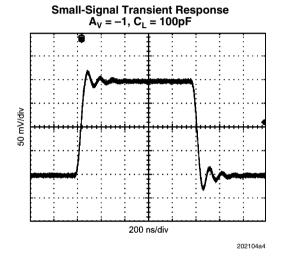
Output Voltage vs Load Resistance V_{CC} = 17V, V_{EE} = -17V, THD+N = 1%

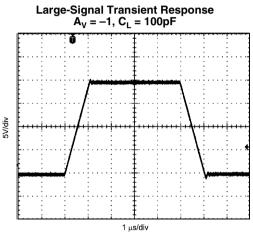


Large-Signal Transient Response



Output Voltage vs Load Resistance V_{CC} = 2.5V, V_{EE} = -2.5V, THD+N = 1%





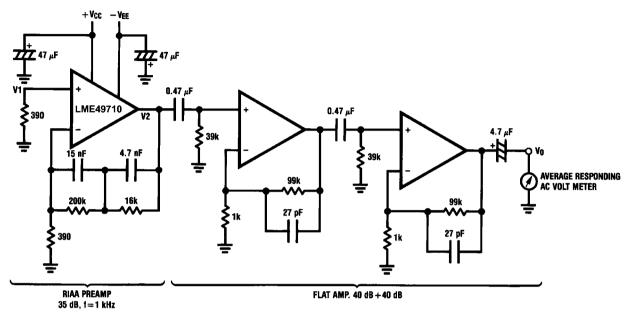
202104a3

Application Hints

The LME49710 is a high speed op amp with excellent phase margin and stability. Capacitive loads up to 100pF will cause little change in the phase characteristics of the amplifiers and are therefore allowable.

Capacitive loads greater than 100pF must be isolated from the output. The most straight forward way to do this is to put a resistor in series with the output. This resistor will also prevent excess power dissipation if the output is accidentally shorted.

Noise Measurement Circuit

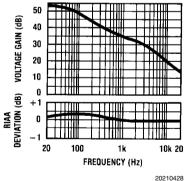


20210427

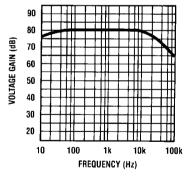
Complete shielding is required to prevent induced pick up from external sources. Always check with oscilloscope for power line noise.

Total Gain: 115 dB at f = 1 kHz Input Referred Noise Voltage: $e_n = V_o/560,000$ (V)

RIAA Preamp Voltage Gain RIAA Deviation vs Frequency V_{IN} = 10mV, A_V = 35.0dB, f = 1kHz

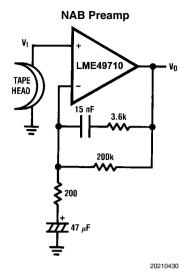


Flat Amp Voltage Gain vs Frequency $V_O = 0$ dB, $A_V = 80.0$ dB, f = 1kHz

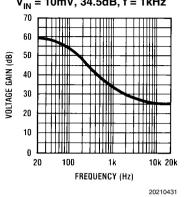


20210429

Typical Applications

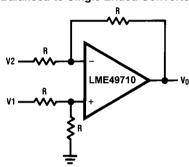


NAB Preamp Voltage Gain vs Frequency V_{IN} = 10mV, 34.5dB, f = 1kHz



 $A_V = 34.5$ F = 1 kHz $E_n = 0.38 \mu\text{V}$ A Weighted

Balanced to Single Ended Converter



20210432

 $V_0 = V1 + V2 - V3 - V4$

Adder/Subtracter

V1

R

V2

R

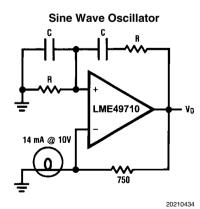
LME49710

V3

R

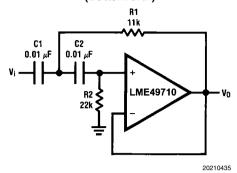
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 $V_O = V1-V2$



 $f_0 = \frac{1}{2\pi RC}$

Second Order High Pass Filter (Butterworth)



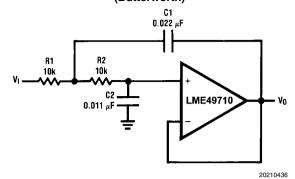
if C1 = C2 = C

$$R1 = \frac{\sqrt{2}}{2\omega_0 C}$$

R2 = 2•R1

Illustration is $f_0 = 1 \text{ kHz}$

Second Order Low Pass Filter (Butterworth)



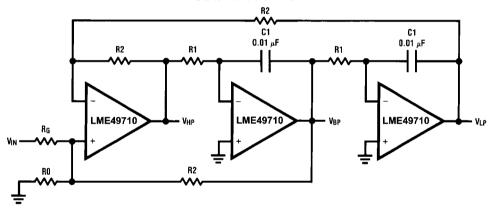
if R1 = R2 = R

$$C1 = \frac{\sqrt{2}}{C \cdot R}$$

$$C2 = \frac{C1}{2}$$

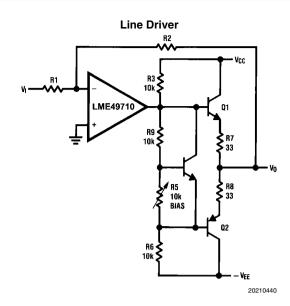
Illustration is f₀ = 1 kHz

State Variable Filter

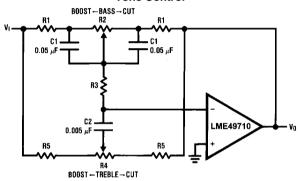


20210437

$$f_0 = \frac{1}{2\pi C1 R1}, Q = \frac{1}{2} \left(1 + \frac{R2}{R0} + \frac{R2}{RG} \right), A_{BP} = QA_{LP} = QA_{LH} = \frac{R2}{RG}$$

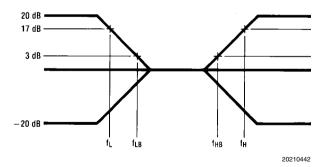


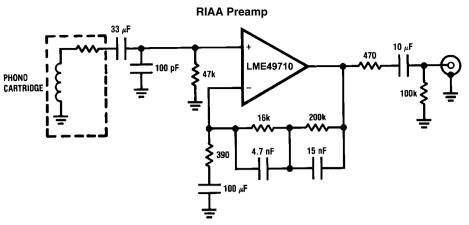
Tone Control



20210441

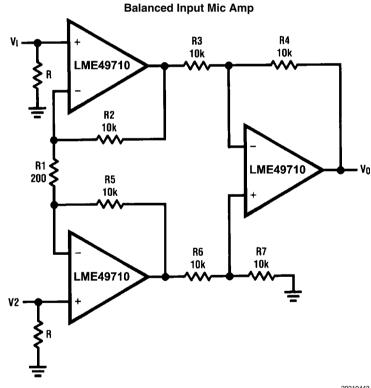
$$\begin{split} & \mathbf{f_L} = \frac{1}{2\pi R2C1}, \, \mathbf{f_{LB}} = \frac{1}{2\pi R1C1} \\ & \mathbf{f_H} = \frac{1}{2\pi R5C2}, \, \mathbf{f_{HB}} = \frac{1}{2\pi (R1 + R5 + 2R3)C2} \end{split}$$





20210403

 $A_v = 35 \text{ dB}$ $E_n = 0.33 \, \mu V$ S/N = 90 dBf = 1 kHzA Weighted A Weighted, V_{IN} = 10 mV @f = 1 kHz



20210443

If R2 = R5, R3 = R6, R4 = R7

$$V0 = \left(1 + \frac{2R2}{R1}\right) \frac{R4}{R3} (V2 - V1)$$

Illustration is: V0 = 101(V2 - V1)

Application Information

DISTORTION MEASUREMENTS

The vanishingly low residual distortion produced by LME49710 is below the capabilities of all commercially available equipment. This makes distortion measurements just slightly more difficult than simply connecting a distortion meter to the amplifier's inputs and outputs. The solution, however, is quite simple: an additional resistor. Adding this resistor extends the resolution of the distortion measurement equipment.

The LME49710's low residual distortion is an input referred internal error. As shown in Figure 2, adding the 10Ω resistor connected between the amplifier's inverting and non-inverting

inputs changes the amplifier's noise gain. The result is that the error signal (distortion) is amplified by a factor of 101. Although the amplifier's closed-loop gain is unaltered, the feedback available to correct distortion errors is reduced by 101, which means that measurement resolution increases by 101. To ensure minimum effects on distortion measurements, keep the value of R1 low as shown in Figure 2.

This technique is verified by duplicating the measurements with high closed loop gain and/or making the measurements at high frequencies. Doing so produces distortion components that are within the measurement equipment's capabilities. This datasheet's THD+N and IMD values were generated using the above described circuit connected to an Audio Precision System Two Cascade.

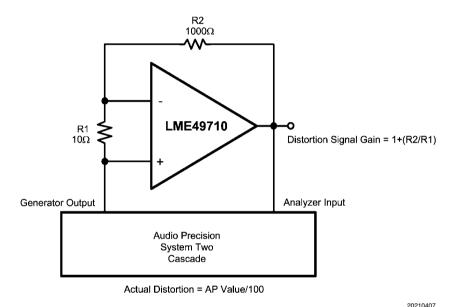
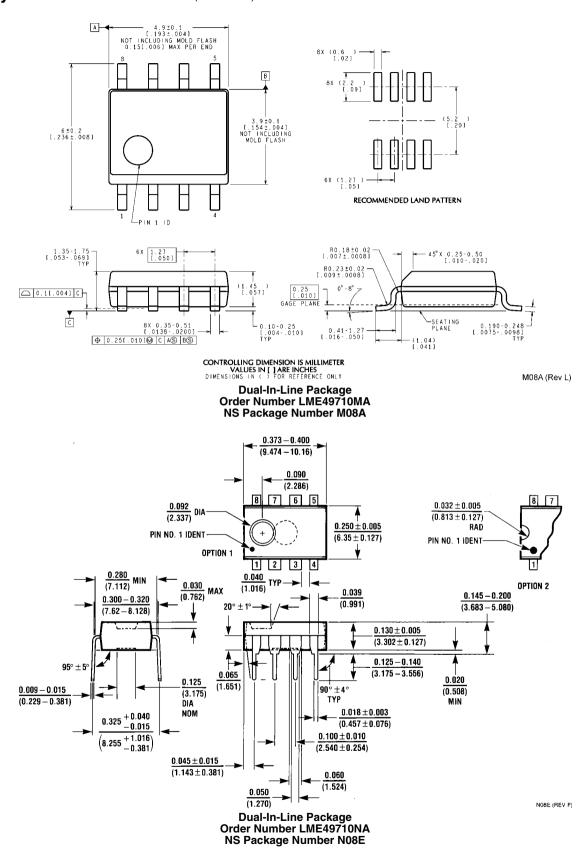


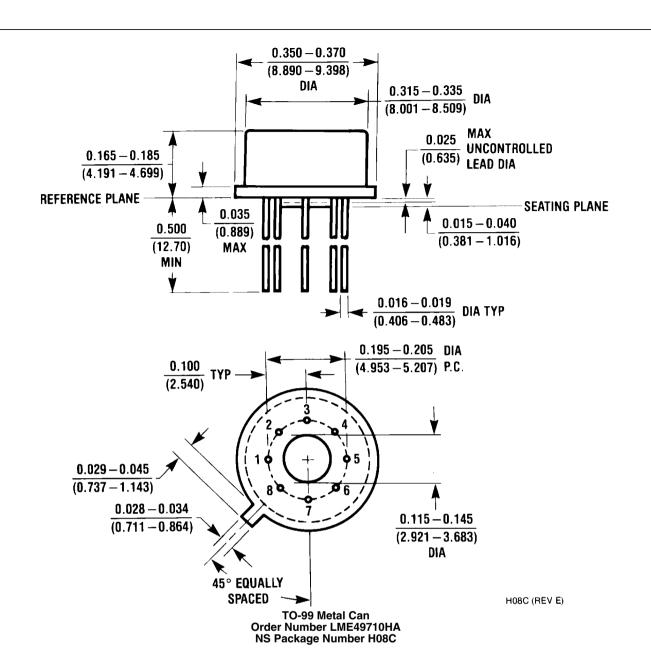
FIGURE 2. THD+N and IMD Distortion Test Circuit

Revision History

Rev	Date	Description	
1.0	11/16/07	Initial release.	
1.1	12/12/06	Added the Typical Performance	
		curves.	
1.2	01/15/07	Added more curves and input some text edits.	
1.3	03/09/07	Fixed graphics 20210489 and 90.	

Physical Dimensions inches (millimeters) unless otherwise noted





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Notes

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